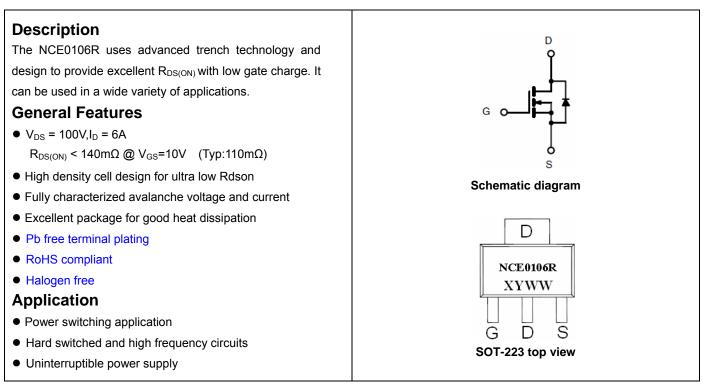


NCE N-Channel Enhancement Mode Power MOSFET



Package Marking and Ordering Information

		0			
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0106R	NCE0106R	SOT-223-3L	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	100	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	6	A
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	4.2	A
Drain Current-Pulsed (Note 1)	I _{DM}	24	A
Maximum Power Dissipation	PD	3	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{θJA}	71	°C/W
Thermal Resistance, Junction-to-Case (Note 2) (Drain)	$R_{ extsf{ heta}JC}$	41.7	°C/W

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V Ι _D =250μΑ	100	110	-	V



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NCE0106R

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.2	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5A	-	110	140	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =5A	-	8	-	S
Dynamic Characteristics (Note4)				J		
Input Capacitance	C _{Iss}		-	690	-	PF
Output Capacitance	Coss	V _{DS} =25V,V _{GS} =0V, F=1.0MHz	-	120	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHZ	-	90	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	11	-	nS
Turn-on Rise Time	tr	V_{DD} =50V, R _L =15 Ω	-	7.4	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =2.5 Ω	-	35	-	nS
Turn-Off Fall Time	t _f		-	9.1	-	nS
Total Gate Charge	Qg		-	15.5		nC
Gate-Source Charge	Q _{gs}	V_{DS} =50V,I _D =5A,	-	3.2	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	4.7	-	nC
Drain-Source Diode Characteristics			I			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =6A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	6	Α

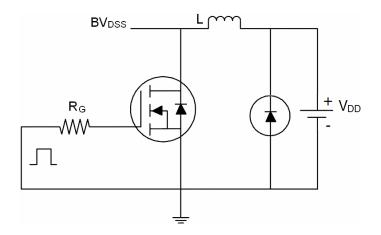
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, t \leq 10 sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to product

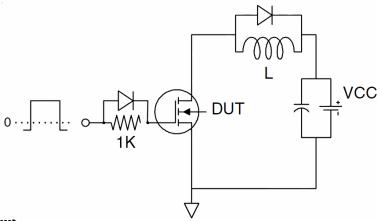


Test Circuit

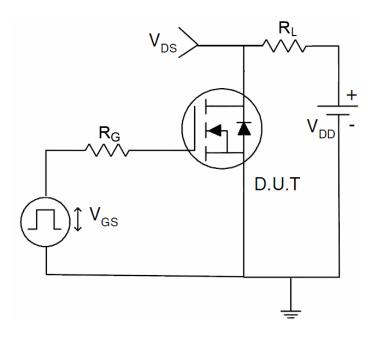
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (curves)

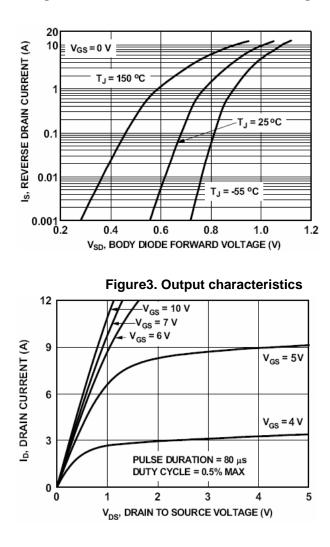


Figure1. Source-Drain Diode Forward Voltage

Figure2. Safe operating area

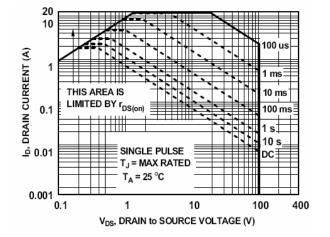


Figure4. Transfer characteristics

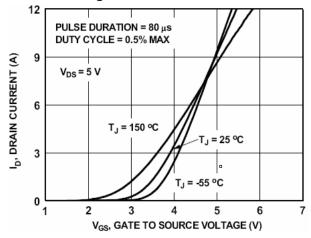
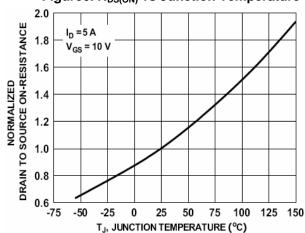
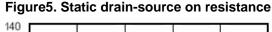
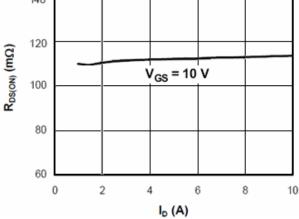


Figure6. R_{DS(ON)} vs Junction Temperature







BVDSS Vcs(th) (norm) (norm) V_{gs}=0 I₀=250µA V_{DS}=V_{GS} 1.2 1.0 Io=250μA 0.9 1.1 1.0 0.8 0.9 0.7 0.8 0.6 50 -50 100 50 0 TJ(°C) -50 0 100 TJ(°C) Figure9. Gate charge waveforms Figure10. Capacitance 10 1000 Ciss V_{DS}= 50 V I_D =5 A 8 100 V_{GS} (Volts) 6 CAPACITANCE (pF) 4 10 2 = 1 MHz V_{GS} = 0 V 0 0 5 10 15 20 25 30 1 0.1 10 100 1 Q_g (nC) V_{DS}, DRAIN TO SOURCE VOLTAGE (V) 2 DUTY CYCLE-DESCENDING ORDER 1 D = 0.5 FH 0.2 r(t),Normalized Effective Transient Thermal Impedance 0.1 ۲ 0.05 0.1 0.02 ₮ PDM 0.01 +╈ 0.01 SINGLE PULSE NOTES: DUTY FACTOR: $D = t_1/t_2$ $R_{\theta JA} = 41.7^{\circ}C/W$ PEAK $T_J = P_{DM} \times Z_{\theta JA} \times R_{\theta JA} + T_A$ 0.001 100 1000 . 10⁻⁴ 10⁻³ 10⁻² 10⁻¹ 10 1 Square Wave Pulse Duration (sec)

Figure7. BV_{DSS} vs Junction Temperature

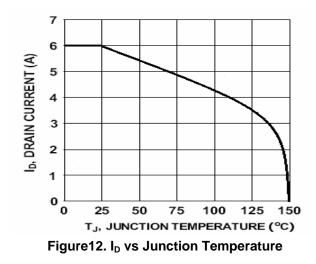
行力运

Figure8. V_{GS(th)} vs Junction Temperature



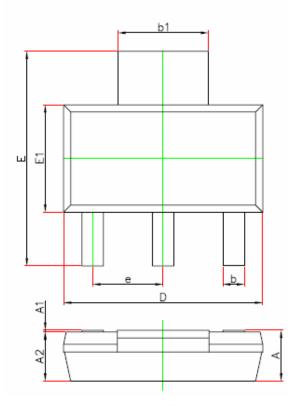
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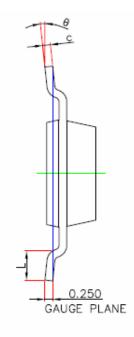
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SOT-223 Package Information





Symbol	Dimensions In	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А		1.800		0.071	
A1	0.020	0.100	0.001	0.004	
A2	1.500	1.700	0.059	0.067	
b	0.660	0.840	0.026	0.033	
b1	2.900	3.100	0.114	0.122	
с	0.230	0.350	0.009	0.014	
D	6.300	6.700	0.248	0.264	
E	6.700	7.300	0.264	0.287	
E1	3.300	3.700	0.130	0.146	
е	2.300(BSC)		0.091(BSC)		
L	0.750		0.030		
θ	0°	10°	0°	10°	

Notes

1. All dimensions are in millimeters.

2. Tolerance ± 0.10 mm (4 mil) unless otherwise specified

3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.

4. Dimension L is measured in gauge plane.

5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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